

14701 Firestone Blvd * La Mirada, Ca 90638 Phone: (562) 404-7855 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

1N4148SM

200 mAMP 75 Volts 5 nsec HYPER FAST RECTIFIER

DESIGNER'S DATA SHEET

Part Number / Ordering Information 1/

1N4148SM__

L Screening^{2/} = None TX = TX Level TXV = TXV Level S = S Level

L Package

SM = **Surface Mount Round Tab**

Features:

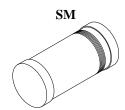
- Hyper Fast Recovery: 5 nsec Max.
- Subminiature Surface Mount Package
- Round Tab Mounting (Square Tabs Available)
- Hermetically Sealed
- Planar Passivated Chip
- For High Efficiency Applications
- TX, TXV, and S-Level Screening Available^{2/}

Maximum Ratings	Symbol	Value	Units
Peak Repetitive Reverse and DC Blocking Voltage	$egin{array}{c} \mathbf{V_{RRM}} \ \mathbf{V_{RWM}} \ \mathbf{V_{R}} \end{array}$	75	Volts
Average Rectified Forward Current (Resistive Load, 60 Hz, Sine Wave, T _A = 25°C)	Io	200	mAmps
Surge Current (8.3 ms Pulse, Half Sine Wave Superimposed on Io, Allow Junction to Reach Equilibrium between Pulses, $T_A = 25^{\circ}C$)	$I_{ m FSM}$	2	Amps
Operating & Storage Temperature	Top & Tstg	-65 to +200	°C
Maximum Thermal Resistance Junction to End Tab	$R_{ heta JE}$	0.35	°C/mW

Notes:

1/ For Ordering Information, Price, Operating Curves, and Availability – Contact Factory.

2/ Screening Based on MIL-PRF-19500. Screening Flows Available on Request.





Solid State Devices, Inc.

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Electrical Characteristics		Symbol	Max	Units
Instantaneous Forward Voltage Drop (T _A = 25°C, 300-500 µs pulse)	$I_F = 10mA$ $I_F = 100mA$	$egin{array}{c} \mathbf{V_{F1}} \ \mathbf{V_{F2}} \end{array}$	0.8 1.2	V_{DC}
Instantaneous Forward Voltage Drop (300-500 µs pulse)	$I_F = 10 \text{mA}, T_A = 150 ^{\circ}\text{C}$ $I_F = 100 \text{mA}, T_A = -55 ^{\circ}\text{C}$	$egin{array}{c} \mathbf{V_{F3}} \ \mathbf{V_{F4}} \end{array}$	0.8 1.3	V _{DC}
Reverse Leakage Current (T _A = 25°C, 300 µs pulse minimum)	$V_R = 20V$ $V_R = 75V$	$egin{array}{c} I_{R1} \ I_{R2} \end{array}$	25 500	nA
Reverse Leakage Current (T _A = 150°C, 300 μs pulse minimum)	$V_R = 20V$ $V_R = 75V$	$egin{array}{c} I_{R3} \ I_{R4} \end{array}$	35 75	μА
Junction Capacitance $(V_R = 1.5 V_{DC}, T_A = 25^{\circ}C, f = 1MHz)$		C_{J}	2.8	pF
Reverse Recovery Time $(I_F = 10 \text{ mA}, I_R = 10\text{mA}, I_{RR} = 1\text{mA}, T_A = 25^{\circ}\text{C})$		t_{rr}	5	nsec

